NIKO-SEM

N-Channel Enhancement Mode Field Effect Transistor

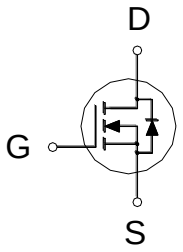
P0610BTF

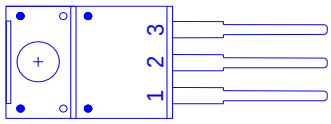
TO-220F

Halogen-Free & Lead-Free

PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
100V	6.5mΩ	66A





1: GATE
2: DRAIN
3: SOURCE

ABSOLUTE MAXIMUM RATINGS (T_A = 25 ° C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	100	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C = 25 ° C	I_D	66	A
	T_C = 100 ° C		41	
Pulsed Drain Current[1]		I_{DM}	200	
Avalanche Current		I_{AS}	40	
Avalanche Energy	L = 1mH	E_{AS}	832	mJ
MOSFET dV/dt Ruggedness		dV/dt	7.7	V/nS
Peak Diode Recovery dV/dt[2]			3	
Power Dissipation	T_C = 25 ° C	P_D	62.5	W
	T_C = 100 ° C		25	
Junction & Storage Temperature Range		T_J, T_{stg}	-55 to 150	° C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient	$R_{\theta JA}$		62.5	° C / W
Junction-to-Case	$R_{\theta JC}$		2	

[1]Pulse width limited by maximum junction temperature.
[2]ID=20A,di/dt=100A/uS,VDD<BVdss,Starting,Tj=25℃.

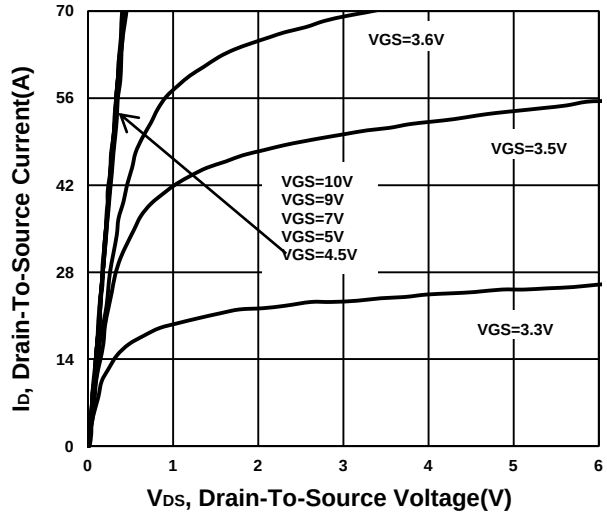
.ELECTRICAL CHARACTERISTICS (T_J = 25 ° C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 250μA	100			V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	1.3	1.8	2.3	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0V, V_{GS} = ±20V			±100	nA

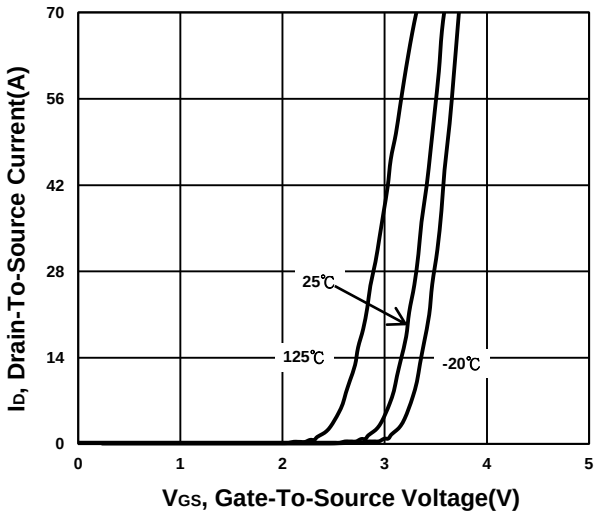
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 80V, V_{GS} = 0V			1	μA
		V_{DS} = 80V, V_{GS} = 0V, T_J = 125℃			10	
Drain-Source On-State Resistance[1]	$R_{DS(ON)}$	V_{GS} = 4.5V, I_D = 20A		6	8	mΩ
		V_{GS} =10V, I_D = 20A		5.4	6.5	
Forward Transconductance[1]	g_{fs}	V_{DS} = 5V, I_D = 20A		133		S
DYNAMIC						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz		6300		pF
Output Capacitance	C_{oss}			744		
Reverse Transfer Capacitance	C_{rss}			219		
Gate Resistance	R_g	V_{GS} = 0V, V_{DS} = 0V, f = 1MHz		1.3		Ω
Total Gate Charge[2]	$Q_{g(VGS=10V)}$	V_{DS} = 50V , I_D =20A		120		nC
	$Q_{g(VGS=4.5V)}$			63		
Gate-Source Charge[2]	Q_{gs}			19.5		
Gate-Drain Charge[2]	Q_{gd}			38		
Turn-On Delay Time[2]	$t_{d(on)}$	V_{DS} = 50V , I_D ≅ 20A, V_{GS} = 10V, R_{GEN} =6Ω		21		nS
Rise Time[2]	t_r			61		
Turn-Off Delay Time[2]	$t_{d(off)}$			54		
Fall Time[2]	t_f			58		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_J = 25 ° C)						
Continuous Current	I_S				52	A
Forward Voltage[1]	V_{SD}	I_F = 20A, V_{GS} = 0V			1.2	V
Diode Reverse Recovery Time	t_{rr}	I_F= 20A, dI/dt=100A/μs		65		nS
Diode Reverse Recovery Charge	Q_{rr}			176		nC

[1]Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.
[2]Independent of operating temperature.

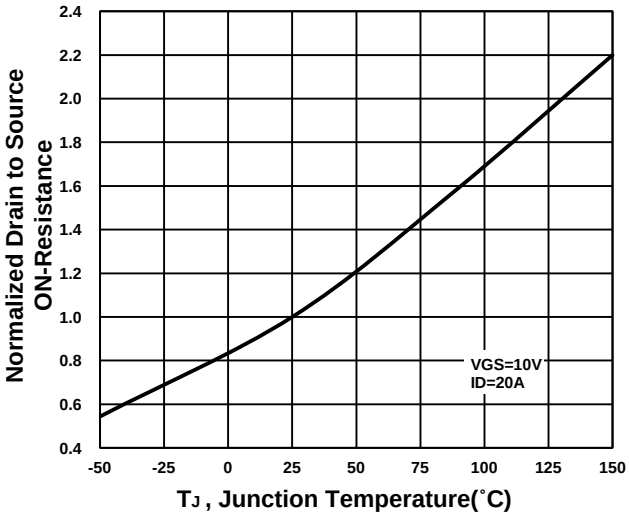
Output Characteristics



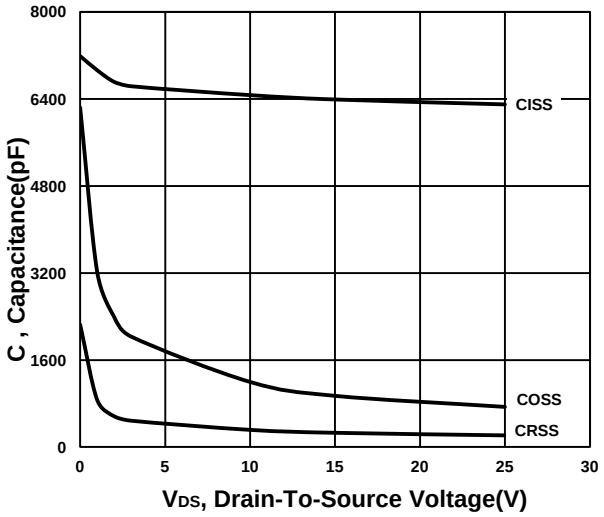
Transfer Characteristics



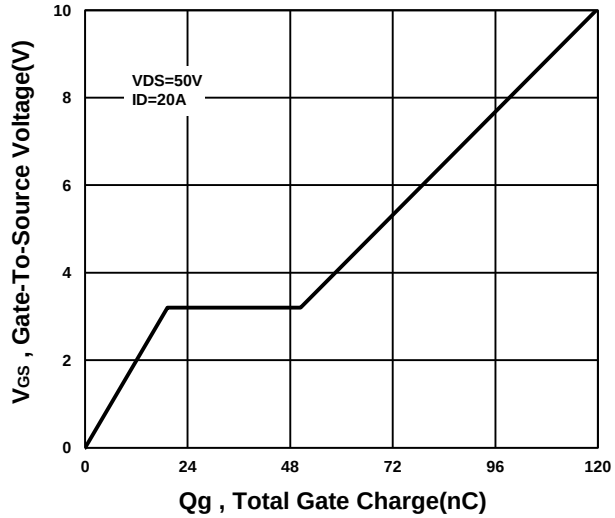
On-Resistance VS Temperature



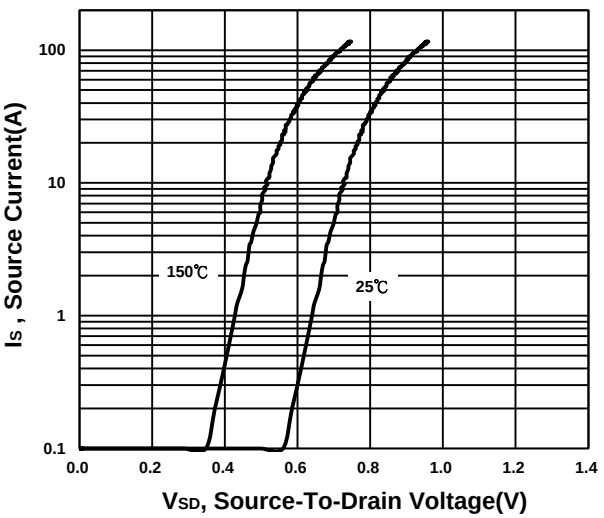
Capacitance Characteristic



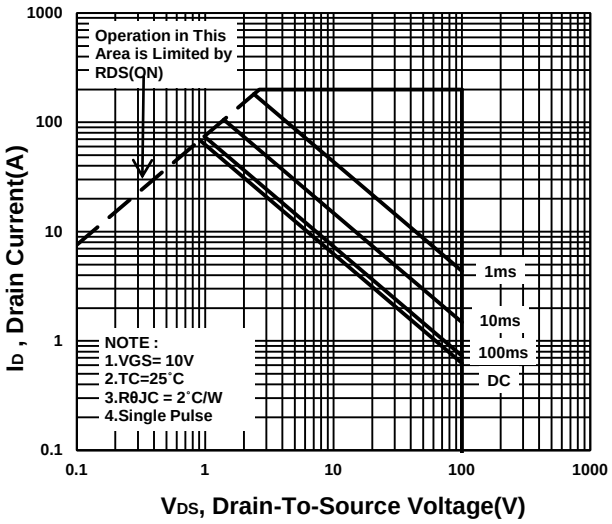
Gate charge Characteristics



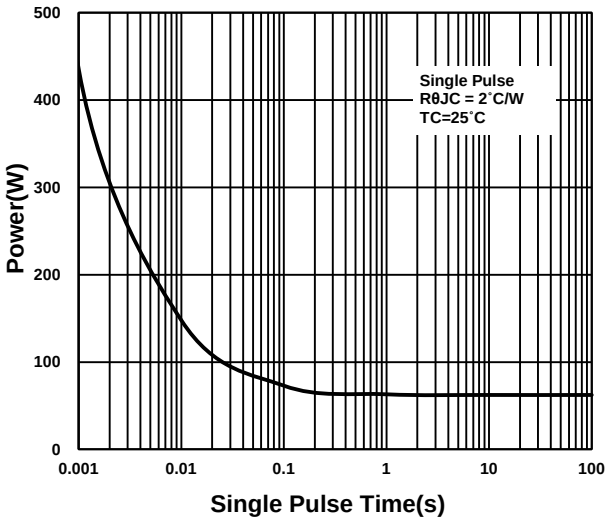
Source-Drain Diode Forward Voltage



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve